

60 V, N-channel Trench MOSFET 4 March 2016

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	2.1	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 2.1 A; T _j = 25 °C		-	96	123	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information						
Type number						
	Name	Description	Version			
PMV120ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV120ENEA	DX%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	2.1	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.3	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	8.3	А
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.3 A; DUT in avalanche (unclamped)		-	9	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	513	mW
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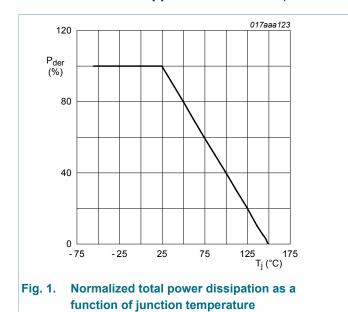
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60 V, N-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	1.05	W
		T _{sp} = 25 °C		-	6.4	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	0.8	А
ESD maxim	um rating		I.			
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

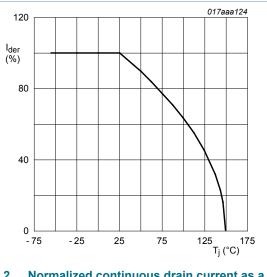
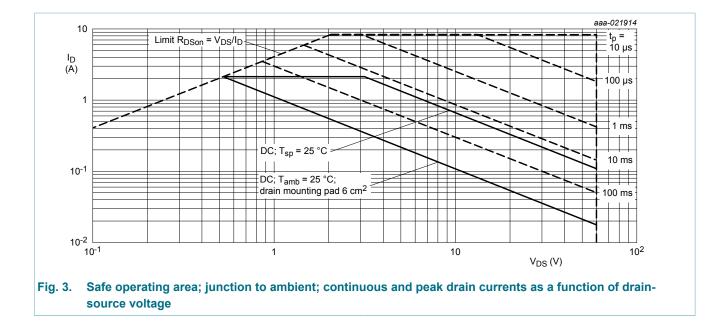


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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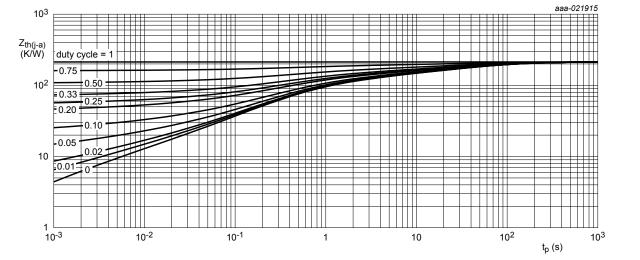


9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance	in free air	[1]	-	212	244	K/W
	from junction to ambient		[2]	-	104	119	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

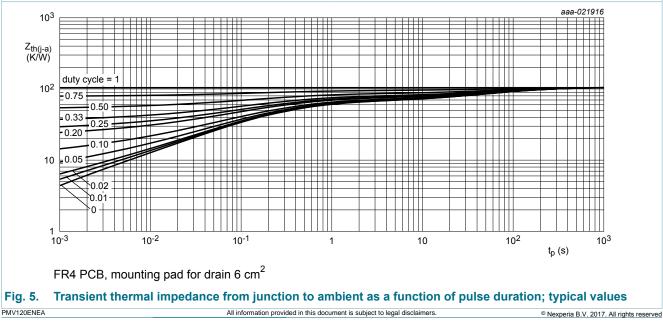
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

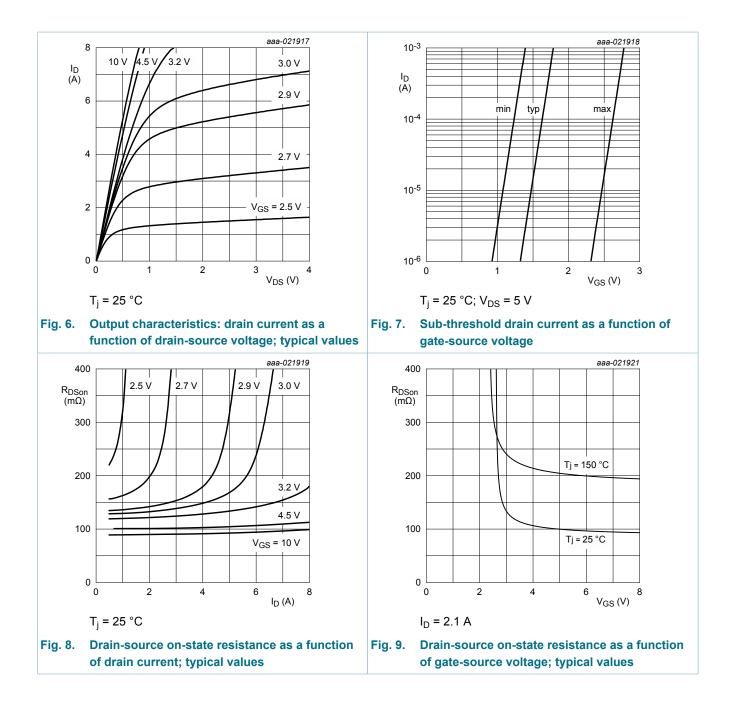




10. Characteristics

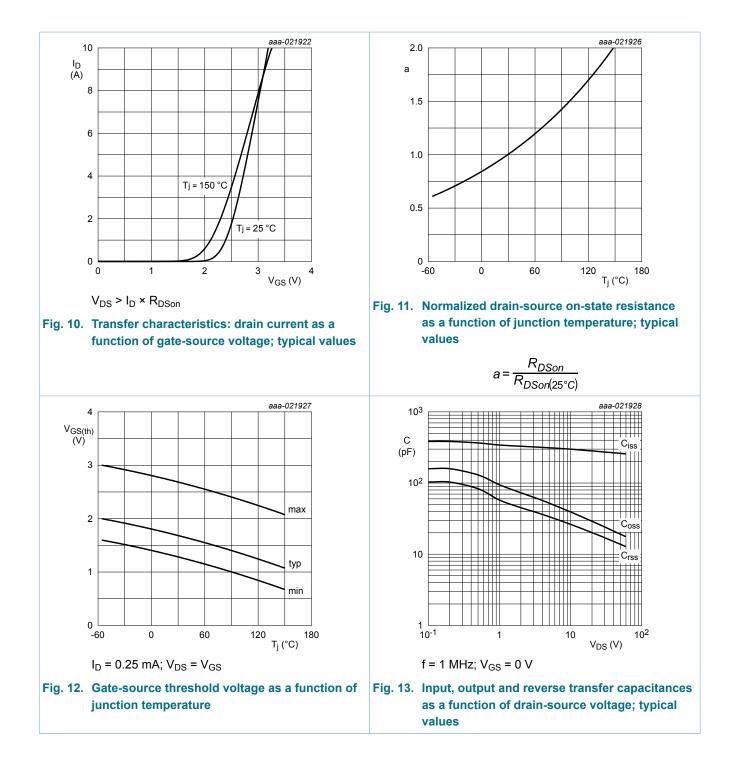
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS} gate leaka	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 2.1 A; T _j = 25 °C	-	96	123	mΩ
	resistance	V _{GS} = 10 V; I _D = 2.1 A; T _j = 150 °C	-	192	246	mΩ
		V _{GS} = 4.5 V; I _D = 1.9 A; T _j = 25 °C	-	108	146	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 0.9 A; T _j = 25 °C	-	10.2	-	S
R _G	gate resistance	f = 1 MHz	-	10	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I _D = 2.1 A; V _{GS} = 10 V;	-	5.9	7.4	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.6	-	nC
Q _{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	V_{DS} = 30 V; f = 1 MHz; V_{GS} = 0 V;	-	275	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	24	-	pF
C _{rss}	reverse transfer capacitance		-	17	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; I _D = 2.1 A; V _{GS} = 10 V;	-	6.4	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	8.9	-	ns
t _{d(off)}	turn-off delay time		-	15.9	-	ns
t _f	fall time		-	6.3	-	ns
Source-drai	n diode		I		1	
V _{SD}	source-drain voltage	I _S = 0.8 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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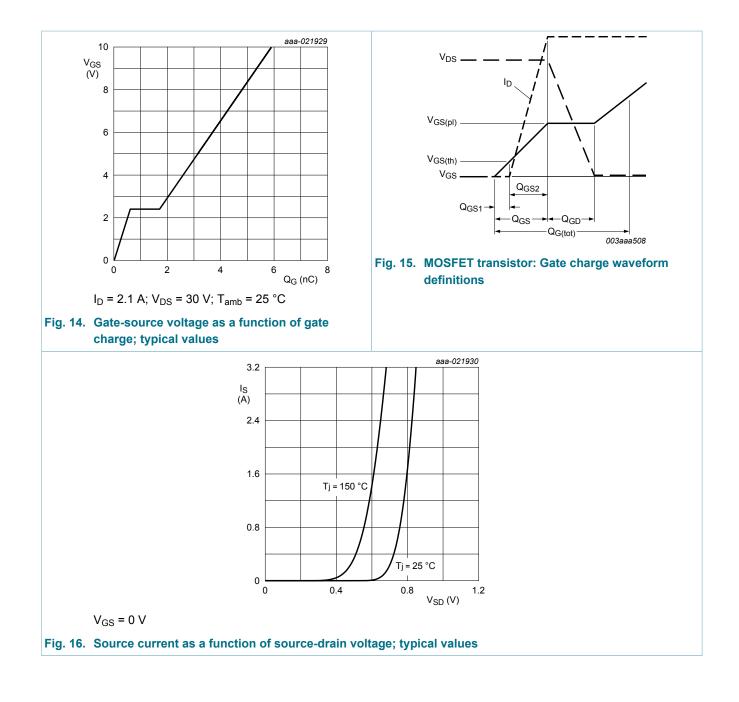
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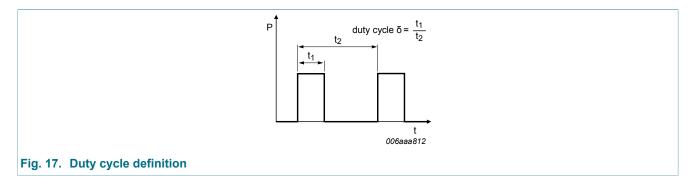
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11. Test information

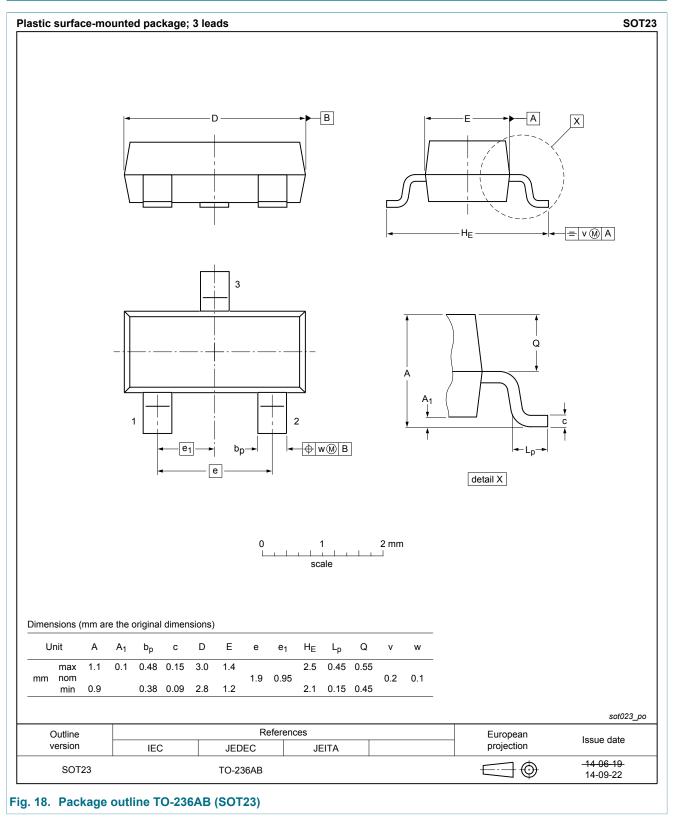


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

60 V, N-channel Trench MOSFET

12. Package outline



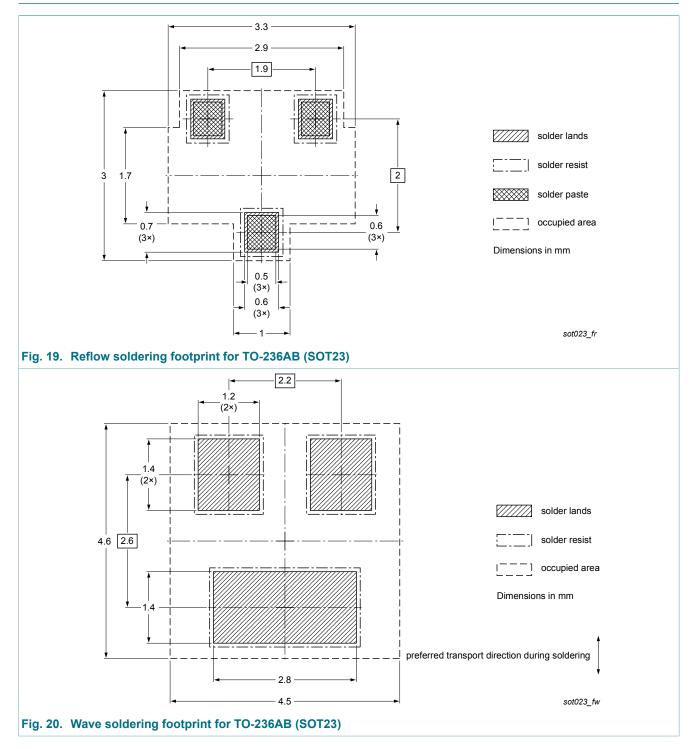
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60 V, N-channel Trench MOSFET

13. Soldering



14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMV120ENEA v.1	20160304	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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60 V, N-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	5
10	Characteristics	6
11	Test information	10
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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